Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S2	1363	(257/52 or 257/53).ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/05/31 08:07
S3	2439	(257/57 or 257/59).ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/05/31 08:13
S4	2347	(257/57 or 257/59).ccls. not S2	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/05/31 08:14
S5	226	(257/57 or 257/59).ccls. not S2 and adhesive	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/05/31 08:17
S6	174	(257/57 or 257/59).ccls. not S2 and adhesive and @ad<"20030130"	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/05/31 08:54
S7	14	(257/E29.289).ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/05/31 08:55
S8	2	(257/E25.001).ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/05/31 08:57
S9	74	(257/E25.01).ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/05/31 08:58
S10	3	(257/E25.004).ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/05/31 08:58
S11	300	(257/E25.032).ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/05/31 09:01
S12	130	(257/E31.096).ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/05/31 09:02
S13	18366	semiconductor and (amorphous or a?si) and ((adhes$5) or (plastic) with (substrate or base))	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/05/31 09:04

S14	11144	semiconductor and (amorphous or a?si) and ((adhes$5 or plastic) with (substrate or base))	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/05/31 09:05
S15	10892	semiconductor and (amorphous or "a-si" or "a:si") and ((adhes$5 or plastic) with (substrate or base))	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/05/31 09:06
S16	1187	semiconductor and ((amorphous or "a-si" or "a:si") with active) and ((adhes$5 or plastic) with (substrate or base))	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/05/31 09:06
S17	1166	semiconductor and ((amorphous or "a-si" or "a:si") with active) and ((adhes$5 or plastic) with (substrate))	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/05/31 09:06
S18	867	semiconductor and ((amorphous or "a-si" or "a:si") with active) and ((adhes$5 or plastic) with (substrate)) and @ad<"20030108"	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/05/31 09:15
S19	475	semiconductor and ((amorphous or "a-si" or "a:si") with active) and ((adhes$5) with (substrate)) and @ad<"20030108"	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/05/31 09:45
S20	543	semiconductor and ((amorphous or "a-si" or "a:si") with active) and ((plastic) with (substrate)) and @ad<"20030108"	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/05/31 09:07
S21	677	semiconductor and ((amorphous or "a-si" or "a:si") with active) and (($5crystal or $5crystalline) with active) and ((adhes$5 or plastic) with (substrate)) and @ad<"20030108"	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/05/31 09:54
S22	137	semiconductor and ((amorphous or "a-si" or "a:si") with active) and ((adhes$5) with (exfoliat$4 or paper or peel$3 or tap$3)) and @ad<"20030108"	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/05/31 09:46
S23	68	semiconductor and ((amorphous or "a-si" or "a:si") with active) and ((adhes$5) with (exfoliat$4 or tap$3)) and @ad<"20030108"	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/05/31 09:46
S24	46	semiconductor and (((amorphous near3 TFT or "a-TFT" or "a:TFT") near5 (connect$5 or contact)) with (TFT)) and @ad<"20030108"	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/05/31 10:03